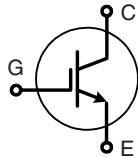


High Voltage IGBT with optional Diode ISOPLUS™ package

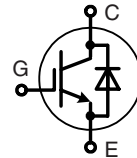
(Electrically Isolated Back Side)

$V_{CES} = 1200\text{ V}$
 $I_{C25} = 50\text{ A}$
 $V_{CE(sat) \text{ typ}} = 2.4\text{ V}$

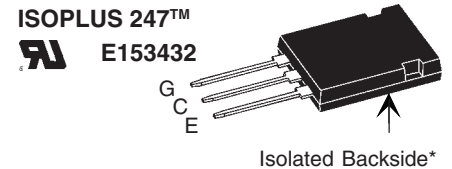
Short Circuit SOA Capability
Square RBSOA



IXDR 30N120



IXDR 30N120 D1



G = Gate C = Collector E = Emitter

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 20\text{ k}\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	50	A
I_{C90}	$T_C = 90^\circ\text{C}$	30	A
I_{CM}	$T_C = 90^\circ\text{C}$, $t_p = 1\text{ ms}$	60	A
RBSOA	$V_{GE} = \pm 15\text{ V}$, $T_J = 125^\circ\text{C}$, $R_G = 47\ \Omega$ Clamped inductive load, $L = 30\text{ mH}$	$I_{CM} = 50$ $V_{CEK} < V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = \pm 15\text{ V}$, $V_{CE} = V_{CES}$, $T_J = 125^\circ\text{C}$ $R_G = 47\ \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	IGBT	200 W
		Diode	95 W
T_J		-55 ... +150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1\text{ mA}$	2500	V~
Weight		6	g

Features

- NPT IGBT technology
- high switching speed
- low switching losses
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- fast recovery epitaxial diode
- Epoxy meets UL 94V-0
- Isolated and UL registered E153432

Advantages

- DCB Isolated mounting tab
- Meets TO-247AD package Outline
- Package for clip or spring mounting
- Space savings
- High power density

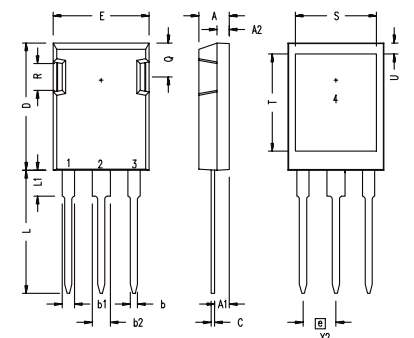
Typical Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{(BR)CES}$	$V_{GE} = 0\text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 1\text{ mA}$, $V_{CE} = V_{GE}$	4.5		V
I_{CES}	$V_{CE} = V_{CES}$, $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			1.5 mA
			2.5	mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			$\pm 500\text{ nA}$
$V_{CE(sat)}$	$I_C = 30\text{ A}$, $V_{GE} = 15\text{ V}$	2.4	2.9	V

Symbol	Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
C _{ies}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		1650	pF
C _{oes}			250	pF
C _{res}			110	pF
Q _g	I _C = 30 A, V _{GE} = 15 V, V _{CE} = 0.5 V _{CES}		120	nC
t _{d(on)}	Inductive load, T _J = 125°C I _C = 30 A, V _{GE} = ±15 V, V _{CE} = 600 V, R _G = 47 Ω		100	ns
t _r			70	ns
t _{d(off)}			500	ns
t _f			70	ns
E _{on}			4.6	mJ
E _{off}		3.4	mJ	
R _{thJC}				0.6 K/W
R _{thCH}	Package with heatsink compound		0.25	K/W

Symbol	Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
V _F	I _F = 30 A, V _{GE} = 0 V		2.5	2.75 V
	I _F = 30 A, V _{GE} = 0 V, T _J = 125°C		2.0	V
I _F	T _C = 25°C			50 A
	T _C = 90°C			27 A
I _{RM}	I _F = 30 A, -di _F /dt = 400 A/μs, V _R = 600 V		20	A
t _{rr}	V _{GE} = 0 V, T _J = 125°C		200	ns
t _{rr}	I _F = 1 A, -di _F /dt = 100 A/μs, V _R = 30 V, V _{GE} = 0 V		40	ns
R _{thJC}				1.3 K/W

ISOPLUS 247 OUTLINE


1 Gate, 2 Drain (Collector)
 3 Source (Emitter)
 4 no connection

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190
S	13.21	13.72	.520	.540
T	15.75	16.26	.620	.640
U	1.65	3.03	.065	.080

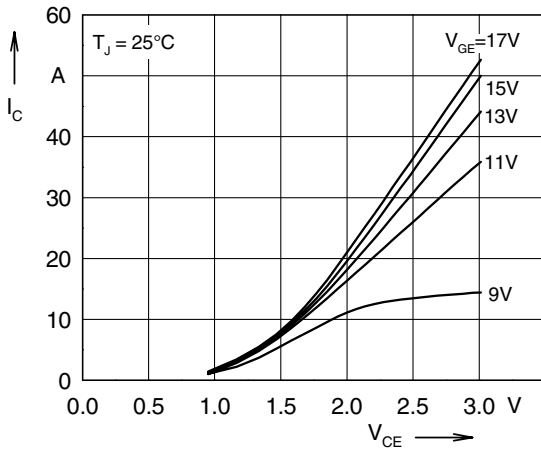


Fig. 1 Typ. output characteristics

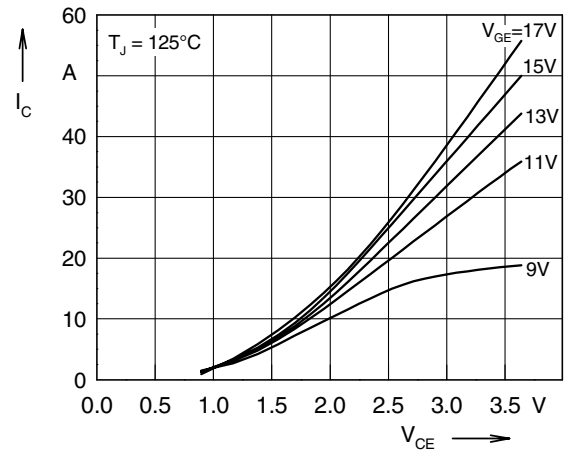


Fig. 2 Typ. output characteristics

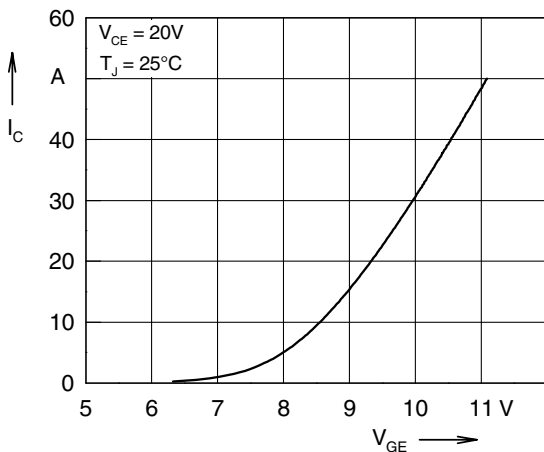


Fig. 3 Typ. transfer characteristics

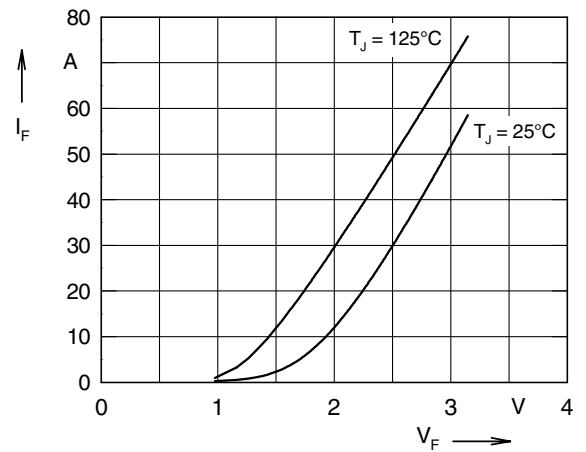


Fig. 4 Typ. forward characteristics of free wheeling diode

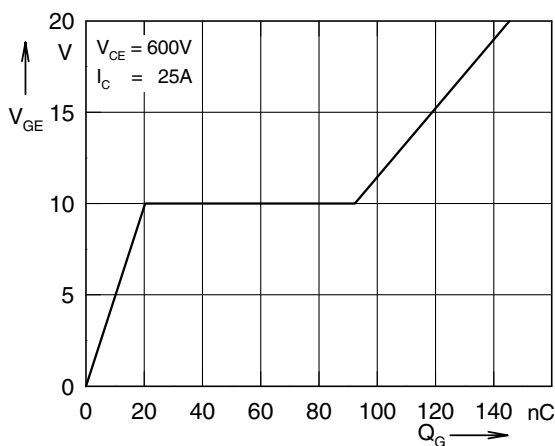


Fig. 5 Typ. turn on gate charge

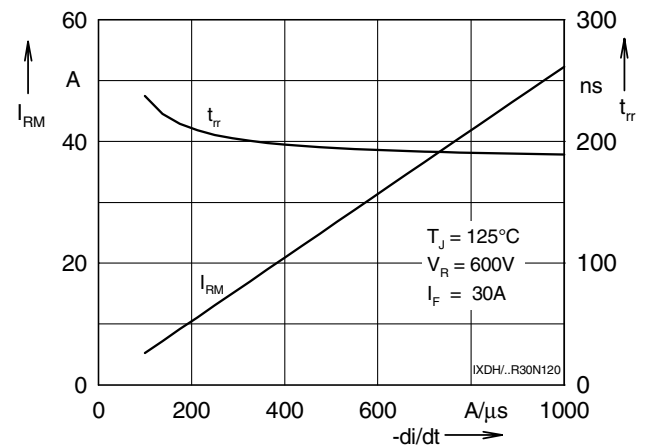


Fig. 6 Typ. turn off characteristics of free wheeling diode

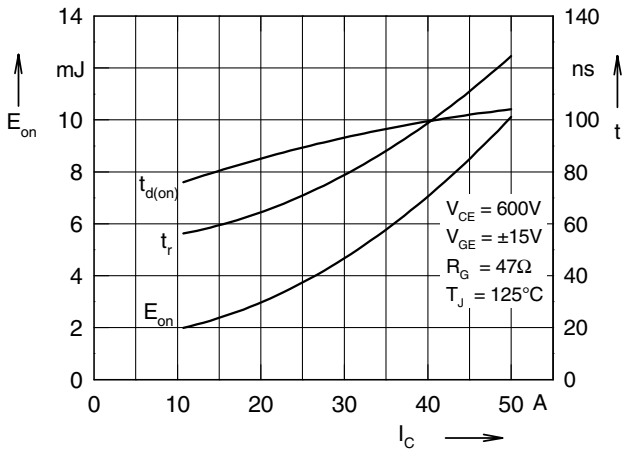


Fig. 7 Typ. turn on energy and switching times versus collector current

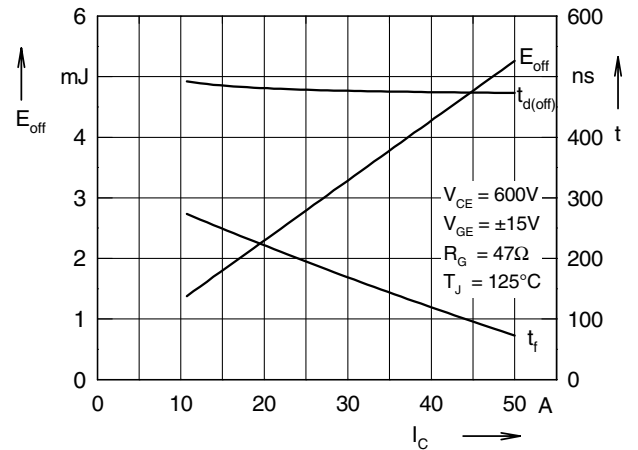


Fig. 8 Typ. turn off energy and switching times versus collector current

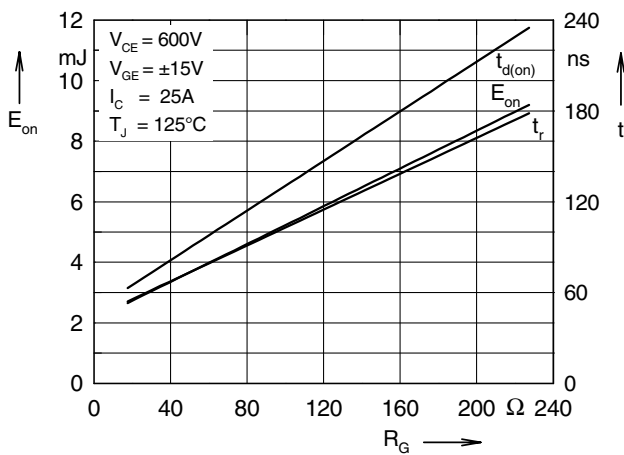


Fig. 9 Typ. turn on energy and switching times versus gate resistor

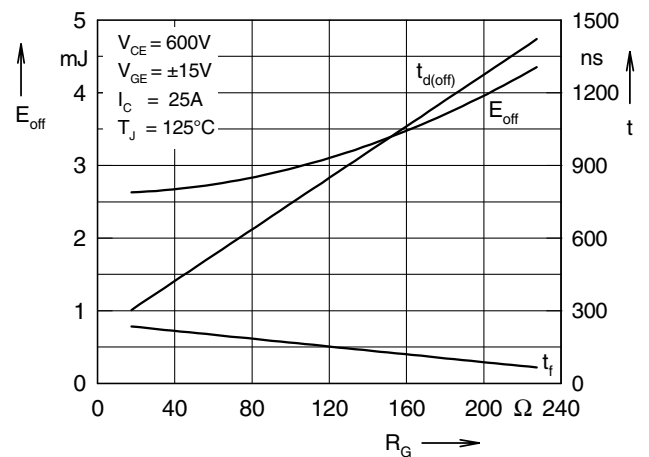


Fig. 10 Typ. turn off energy and switching times versus gate resistor

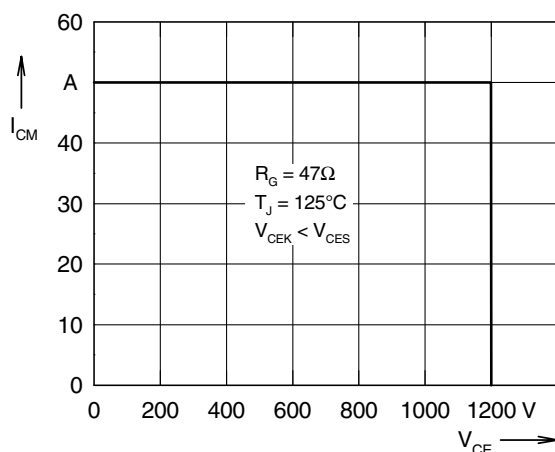


Fig. 11 Reverse biased safe operating area RBSOA

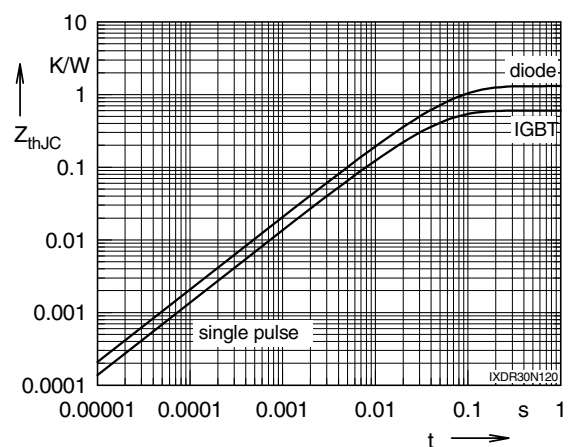


Fig. 12 Typ. transient thermal impedance